ABSTRACT

The present invention is a method for reclaiming a silicon wafer in which a thin film has been formed on its surface, at least, comprising a thin-film removing step for removing the thin film having been formed on the silicon wafer and a mirror-polishing step for mirror-polishing at least one side of the thin-film-removed silicon wafer, wherein, before performing the mirror-polishing step, gettering-site forming treatment for applying damage load to at least one side of the silicon wafer is performed and then the silicon wafer is subjected to heat treatment, thereby impurities inside the silicon wafer are reduced. Thereby, there is provided a method for reclaiming a silicon wafer, in which a thin film such as a metal thin film having been formed on a silicon wafer can be removed, and impurities having diffused inside the wafer can be also reduced, thereby silicon wafers having very little metal contamination can be stably obtained.